

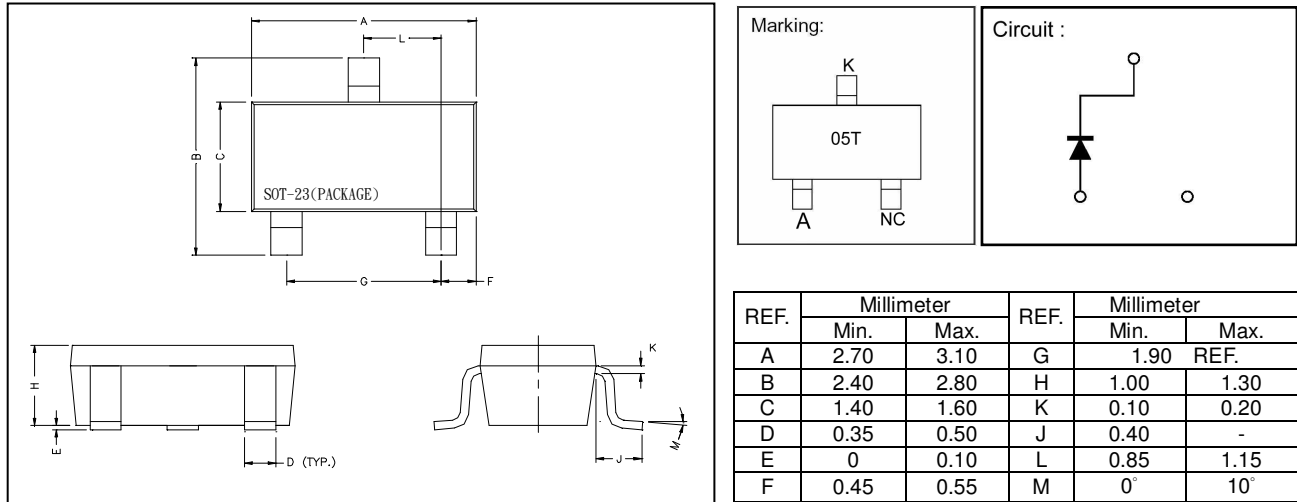
G411SD

SURFACE MOUNT, SCHOTTKY BARRIER DIODE
VOLTAGE 40V, CURRENT 0.5A

Description

The G411SD is designed for low power rectification

Package Dimensions



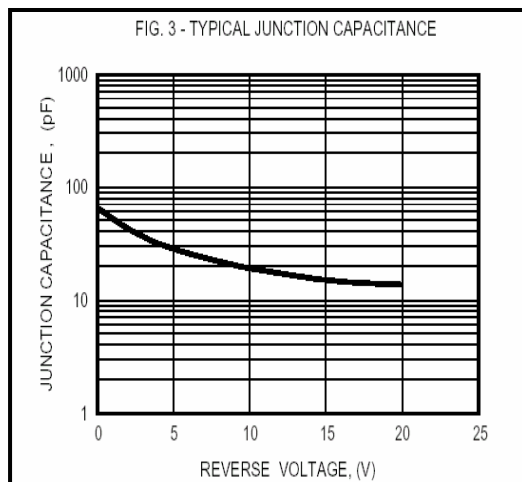
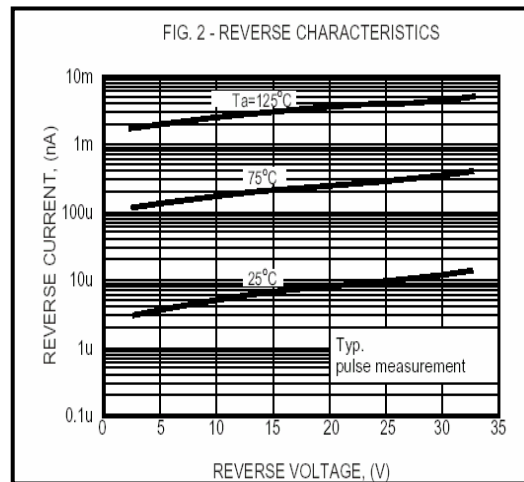
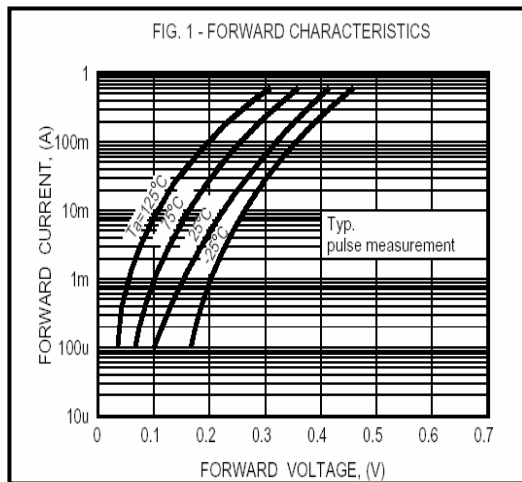
Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+125	°C
Storage Temperature	T _{stg}	-40 ~ +125	°C
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	40	V
Maximum RMS Voltage	V _{RMS}	28	V
Maximum DC Blocking Voltage	V _{DC}	20	V
Peak Forward Surge Current at 8.3mSec single half sine-wave	I _{FSM}	3	A
Typical Junction Capacitance between Terminal	C _J	20	pF
Maximum Average Forward Rectified Current	I _o	0.5	A
Total Power Dissipation	PD	225	mW

Characteristics at Ta = 25°C

Characteristics	Symbol	Typ.	Unit	Test Condition
Maximum Instantaneous Forward Voltage	V _{F(1)}	0.3	V	IF = 10mA
Maximum Instantaneous Forward Voltage	V _{F(2)}	0.5	V	IF = 500mA
Maximum Average Reverse Current	IR	30	uA	VR = 10V

Characteristics Curve



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